

panel for this experiment is an 1-inch. A square driving voltage pulse with a rising time of 200ns and a duty cycle of 25% is applied between the two sustaining electrodes. The driving frequency and pulse width are maintained 7μs at 35kHz, respectively, in this experiment. The width of sustain electrodes is 300 μm and the gap between the sustain electrodes is 50 μm.

3. Results and discussion

The filling gas pressure has been maintained at 400 torr in the experiment. The sustaining voltage has been kept at 310V, 316V, 326V, 330V, and 350 V for XMF of 1%, 4%, 7%, 10% and 15%, respectively. The filling gas pressure has been maintained at 400 torr in the experiment.

Figure 1 shows the VUV intensities of 147 nm and 173 nm versus the xenon mole fraction for binary and ternary gas mixtures of Ne-Xe and He-Ne-Xe. It is observed that the VUV intensity of 147 nm from resonant xenon is found to increase for xenon mole fractions up to 7%, and to be saturated at xenon mole fractions beyond 7%, while the VUV 173 nm from the molecular dimer increases continuously as the xenon concentration increases⁴ from 1% to 15%. Therefore, the ratio of molecular dimer emission 173 nm to resonant emission 147 nm increases rapidly due to density increase of molecular dimer Xe₂* throughout the three-body collision process⁵⁻⁹ for the xenon concentration beyond 7%. It is noted that the VUV 173 nm emitted from the excited molecular dimers still increases with the increasing XMF in this experiment because the dimers scales linearly with the xenon density and these are comparable to those of VUV 147nm under the binary and ternary gas mixtures of Ne-Xe and He-Ne-Xe in this experiment.

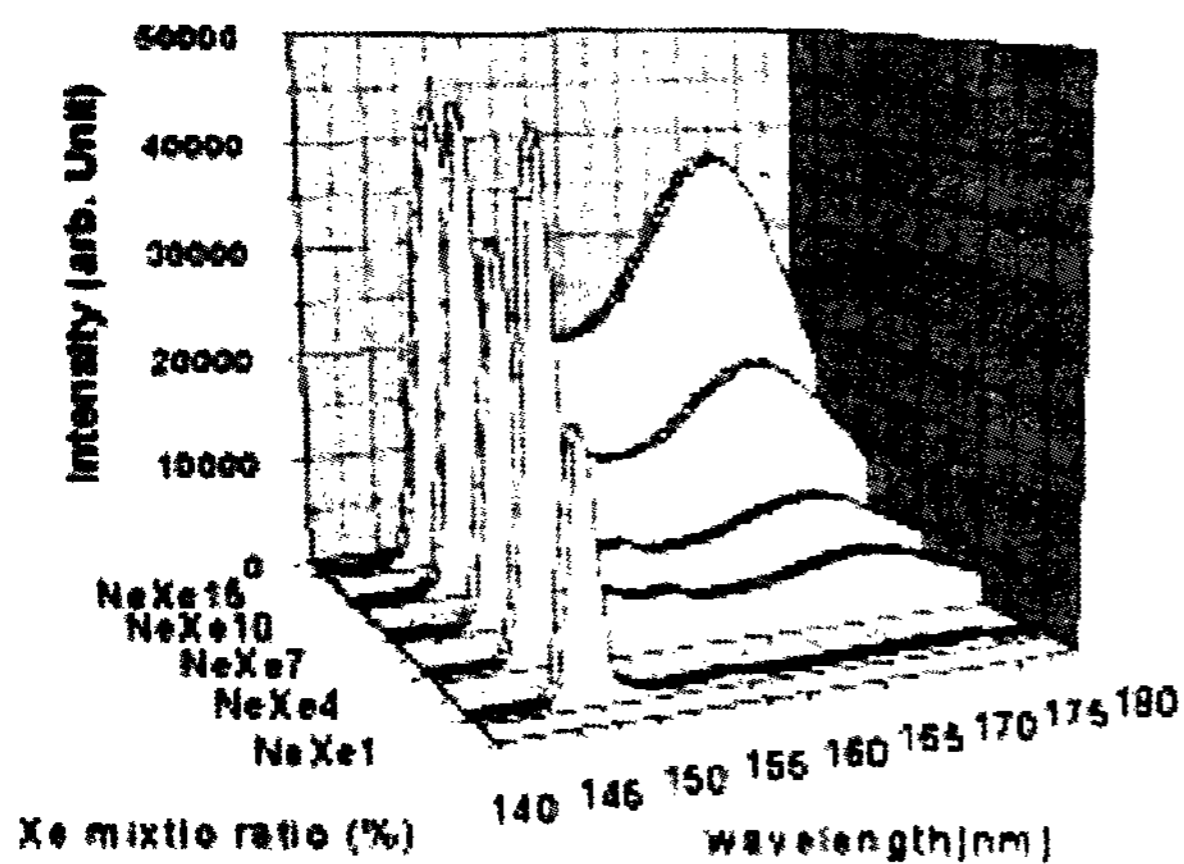


Fig 2(a)

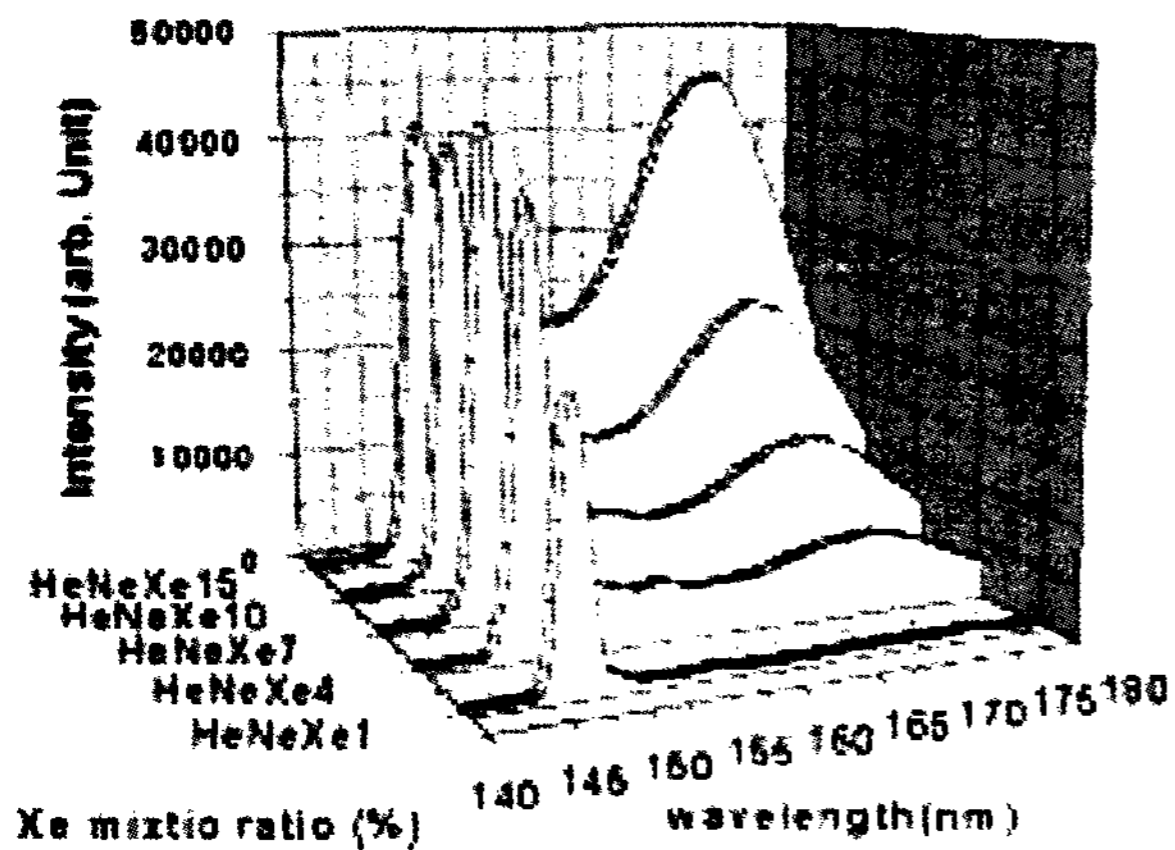


Fig. 2(b)

Fig. 2. Vacuum ultraviolet spectral intensities for Xe mixture ratio of 1%,4%,7%,10% and 15%. (a) Ne-Xe at 400 torr. (b) He(70%)-Ne-Xe at 400 torr.

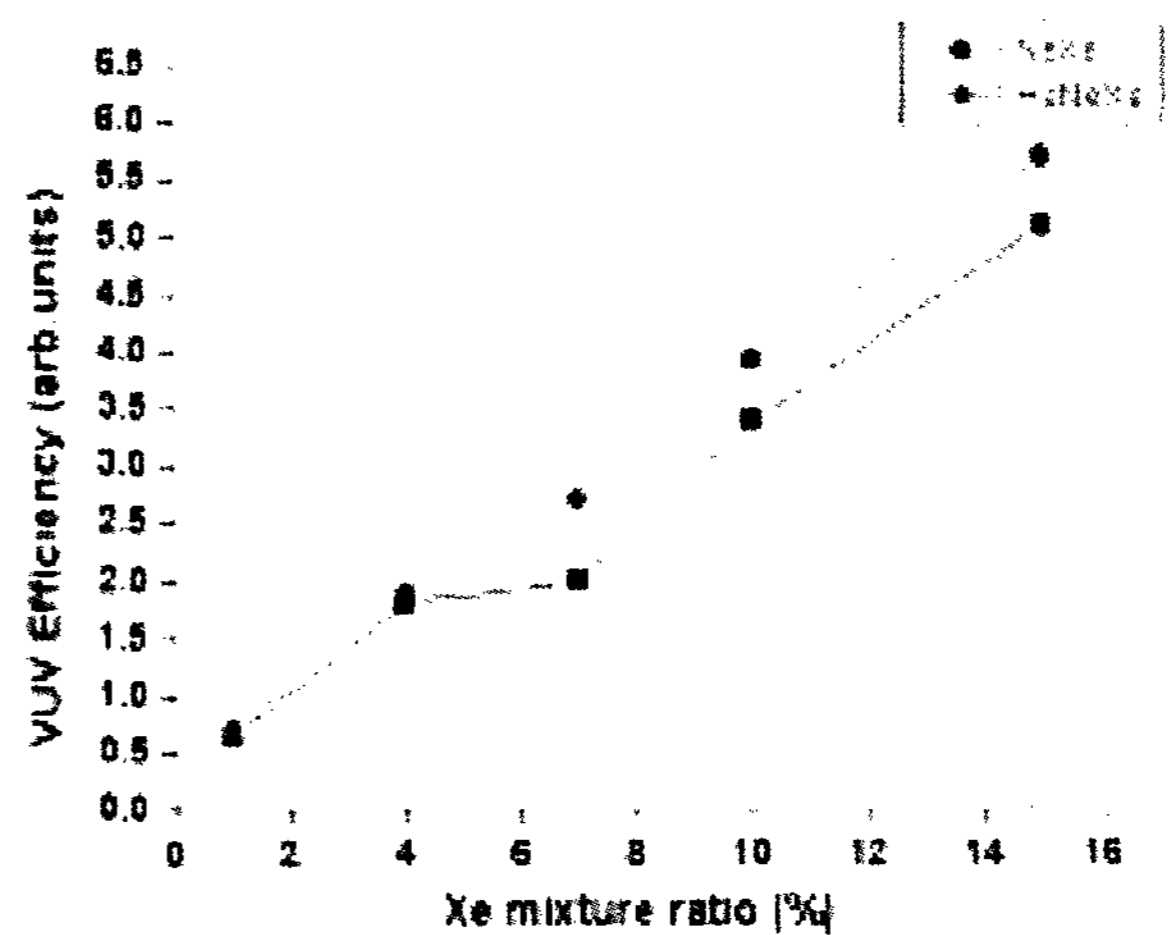


Fig. 2. Vacuum ultraviolet luminous efficiency including both 147 nm and 173 nm versus xenon mole fractions on Ne-Xe and He(70%)-Ne-Xe gas mixtures at 400 torr.

Figure 2 shows the total VUV luminous efficiency including both 147 nm and 173 nm versus XMF. The relative VUV efficiency has been obtained by dividing the integrated VUV intensities from 140 nm to 180nm by the discharge power.⁴ It is found that luminous efficiency of ternary gas mixture, He-Ne-Xe, is shown to be much higher, by an amount of 25%, than that of

binary gas mixture of Ne-Xe for high XMF greater than 7% in this experiment.

4. Conclusion

The influence of binary and ternary gas mixtures of He-Ne-Xe for improvement of vacuum ultraviolet luminous efficiency in ac-PDPs has been investigated. To achieve high luminance and luminous efficiency, high VUV emission efficiency is needed. It is noted that the VUV 173 nm emitted from the excited molecular dimers still increases with the increasing XMF because the dimers scales linearly with the xenon density and these are comparable to those of VUV 147 nm under the binary and ternary gas mixtures of Ne-Xe and He-Ne-Xe. Moreover, the VUV 173 nm emitted from excited molecular dimers of ternary gas mixtures, He-Ne-Xe, are much higher than that of binary gas mixtures, Ne-Xe, with the increasing XMF. The luminous efficiency of ternary gas mixture, He-Ne-Xe, is shown to be much higher, by an amount of 25%, than that of binary gas mixture of Ne-Xe for high XMF greater than 7% in this experiment.

5. References

1. J. C. Ahn, T. Y. Kim, J. J. Ko, Y. Seo, G. S. Cho, and E. H. Choi, *J. Appl. Phys.* 87, 8045 (2000)
2. R. Wendt and H. Lange, *J. Phys. D* 31, 3368 (1998).
3. T. Kamegaya, H. Matsuzaki, *IEEE Trans. Electron Devices* ED-25, 1094 (1978)
4. E. H. Choi, J. C. Ahn, M. W. Moon, Y. Jung, M. C. Choi, Y. H. Seo, G. S. Cho, H. S. Uhm, K. Tachibana, K. W. Whang and M. Kristiansen, *Appl. Phys. Lett.* 81, 3341 (2002)
5. K. Tachibana, S. Feng, and T. Sakai, *J. Appl. Phys.* 88, 4967 (2000).
6. W. J. Alford, *J. Chem. Phys.* 96, 4330 (1992).
7. J. Galy, K. Aouame, A. Birot, H. Brunet, and P. Millet, *J. Phys. B* 26, 477 (1993).
8. W. G. Lee, M. Shao, J. R. Gottschalk, M. Brown, and A. D. Compagn, *J. Appl. Phys.* 92, 682 (2002).
9. M. F. Gillies and G. Oversluizen *J. Appl. Phys.* 91, 6315 (2002)